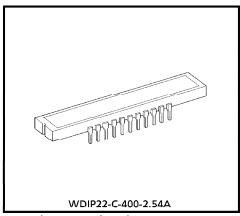
TOSHIBA CCD LINEAR IMAGE SENSOR CCD(Charge Coupled Device)

TCD2300C

The TCD2300C which includes sample-and-hold circuit and clamp circuit is a high sensitive and low dark current 3648 elements × 3 lines CCD color image sensor. The sensor is designed for color scanner.

The device contains a row of 3648 elements × 3 lines photodiodes which provide a 16 lines/mm across a A4 size paper. The device is operated by 5V pulse, and 12V power supply.



FEATURES

• Number of Image Sensing Elements: 3648 elements x 3 lines Weight: 4.8g (Typ.)

Image Sensing Element Size : 8μm by 8μm on 8μm centers
 Photo Sensing Region : High sensitive pn photodiode

Distance Between Photodiode Array : 96μm (12 Lines)
 Clock : 2 phase (5V)

Internal Circuit : Sample & Hold circuit, Clamp circuit

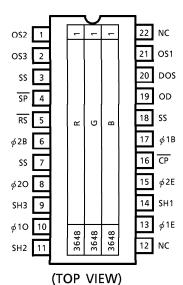
Package : 22 pin DIPColor Filter : Red, Green, Blue

PIN CONNECTIONS

MAXIMUM RATINGS (Note 1)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Clock Pulse Voltage	Vφ			
Shift Pulse Voltage	VsH			
Reset Pulse Voltage	VRS	-0.3~8	V	
Sample and Hold Pulse Voltage	VSP	1		
Clamp Pulse Voltage	VCP			
Power Supply Voltage	V _{OD}	-0.3~15	V	
Operating Temperature	T _{opr}	0~60	°C	
Storage Temperature	T _{stg}	- 25∼85	°C	

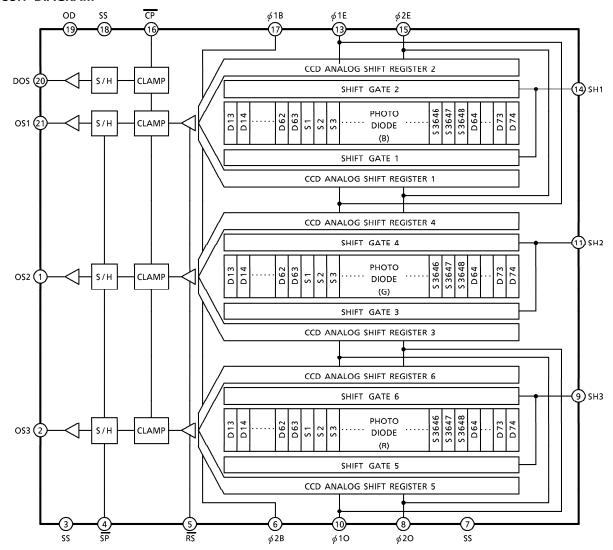
(Note 1) All voltage are with respect to SS terminals (Ground).



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CIRCUIT DIAGRAM



PIN NAMES

<i>φ</i> 1Ε	Clock 1 (Phase 1)	SH3	Shift Gate 3
φ2E	Clock 2 (Phase 2)	RS	Reset Gate
φ1 O	Clock 1 (Phase 1)	SP	Sample and Hold Gate
∮2O	Clock 2 (Phase 2)	CP	Clamp Gate
φ1B	Final Stage Clock (Phase 1)	OS1	Signal Output 1
φ2B	Final Stage Clock (Phase 2)	OS2	Signal Output 2
SS	Ground	OS3	Signal Output 3
OD	Power	DOS	Compensation Output
SH1	Shift Gate 1	NC	Non Connection
SH2	Shift Gate 2		

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OPTICAL / ELECTRICAL CHARACTERISTICS

(Ta = 25°C, V_{OD} = 12V, $V_{\phi} = V_{\overline{RS}} = V_{SH} = V_{\overline{CP}} = 5V$ (Pulse), $f_{\phi} = 0.5 MHz$, $f_{\overline{RS}} = 1.0 MHz$, Load Resistance = 100k Ω , t_{INT} (Integration Time) = 10ms, Light Source = A Light Source + CM500 Filter (t = 1.0mm))

(t = 1.0mm))						
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Sensitivity (Red)	RR	<u> </u>	1.1	_	V / lx·s	(Note 2)
Sensitivity (Green)	RG	_	1.4	_	V / lx·s	(Note 2)
Sensitivity (Blue)	RB	_	0.5	_	V / lx·s	(Note 2)
Photo Posnonso Non Uniformity	PRNU (1)	_	10	20	%	(Note 3)
Photo Response Non Uniformity	PRNU (3)	_	3	12	mV	(Note 4)
Register Imbalance	RI	_	_	3	%	(Note 5)
Saturation Output Voltage	V _{SAT}	1.0	1.5	_	V	(Note 6)
Saturation Exposure	SE	_	1.07	_	lx∙s	(Note 7)
Dark Signal Voltage	V _{DRK}	_	_	2.0	mV	(Note 8)
Dark Signal Non Uniformity	DSNU	_	_	3.0	mV	(Note 9)
Total Transfer Efficiency	TTE	92	_	<u> </u>	%	
Output Impedance	Z _o	_	0.5	1.0	kΩ	
DC Power Dissipation	PD	_	500	_	mW	
DC Offset Voltage	Vos	_	6.0	_	V	(Note 10)
DC Compensation Output Voltage	V _{DOS}	_	6.0	_	V	(Note 10)
DC Mismach Voltage	VOS-VDOS	_	100	300	mV	(Note 10)

- (Note 2) Sensitivity is defined for each color of signal outputs average when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.
- (Note 3) PRNU (1) is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

PRNU (1) =
$$\frac{\Delta \chi}{\overline{\chi}} \times 100$$
 (%)

Where $\overline{\chi}$ is average of total signal outputs and $\Delta \chi$ is the maximum deviation from $\overline{\chi}$.

The amount of the incident light is shown below.

Red =
$$\frac{1}{2}$$
 SE

Green =
$$\frac{1}{2}$$
 SE

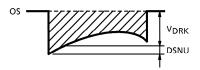
Blue =
$$\frac{1}{4}$$
 SE

- (Note 4) PRNU (3) is defined as maximum voltage with next pixel, where measured 5% of SE (TYP.).
- (Note 5) RI is defined for each color on a single chip by the expressions below when the photosensitive surface is applied with the light of uniform illumination and uniform color temperature.

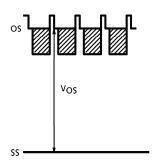
RI =
$$\frac{\sum_{\substack{N=1 \\ 3647 \times \overline{\chi}}} |\chi_N - \chi_N + 1|}{3647 \times \overline{\chi}} \times 100 (\%)$$

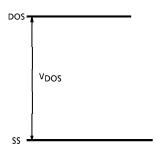
Where x_n and $x_n + 1$ are signal outputs of each pixel. \overline{x} is average of total signal outputs.

- (Note 6) V_{SAT} is defined as minimum Saturation Output Voltage of all effective pixels.
- (Note 7) Definition of SE : SE = $\frac{V_{SAT}}{RG}$
- (Note 8) VDRK is defined as average dark signal voltage of all effective pixels.
- (Note 9) DSNU is defined as different voltage between V_{DRK} and V_{MDK} , when V_{MDK} is maximum dark voltage.



(Note 10) DC Signal Output Voltage and DC Compensation Output Voltage are defined as follows:





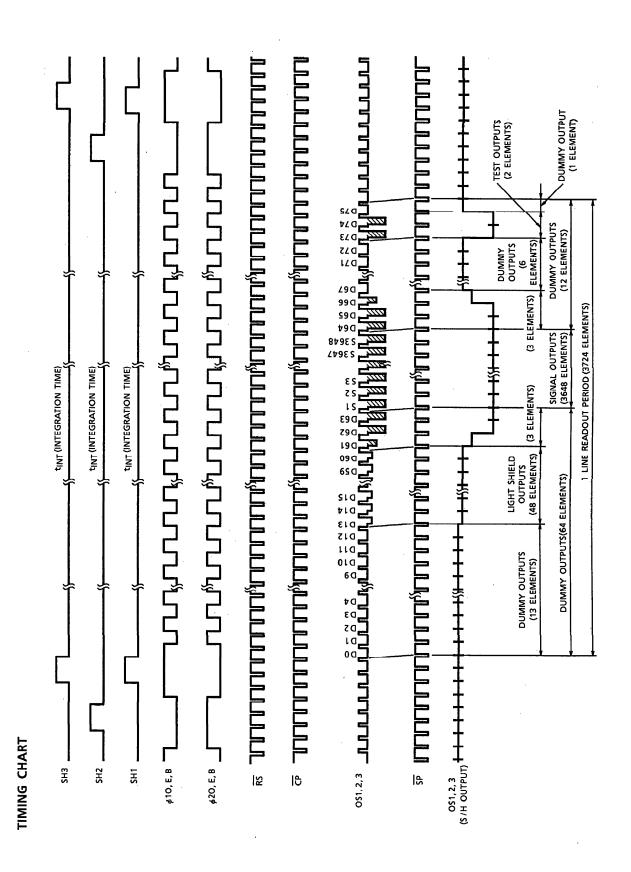
OPERATING CONDITION

CHARACTERISTI	С	SYMBOL	MIN.	TYP.	MAX.	UNIT	NOTE
Clock Pulse Voltage	"H" Level	V ø0, E	4.5	5.0	5.5	V	
Clock Pulse Voltage	"L" Level	νφυ, Ε	0.0	0.2	0.5	'	
Final Stage Clock Pulse	"H" Level	VøB	4.5	5.0	5.5	V	
Voltage	"L" Level	VφB	0.0	0.2	0.5	\ \ \	
Shift Dulco Valtage	"H" Level	Vari	V ø 0,E"H" − 1	Vφ0, Ε "H"	Vø0, E"H"	v	(Note 11)
Shift Pulse Voltage	"L" Level	V _{SH}	0.0	0.2	0.5	V	
Poset Pulse Valtage	"H" Level	—	4.5	5.0	5.5	V	
Reset Pulse Voltage	"L" Level		0.0	0.2	0.5		
Sample and Hold Pulse	"H" Level	\/a=	4.5	5.0	5.5	v	(Note 12)
Voltage	"L" Level	V_{SP}	0.0	0.2	0.5	\ \ \	(14016-12)
Clamp Pulse Voltage	"H" Level	Van	4.5	5.0	5.5	V	(Note 13)
Clamp ruise voltage	"L" Level	V _{CP}	0.0	0.2	0.5	\ \ \	(Note 13)
Power Supply Voltage		V _{OD}	11.4	12.0	13.0	V	

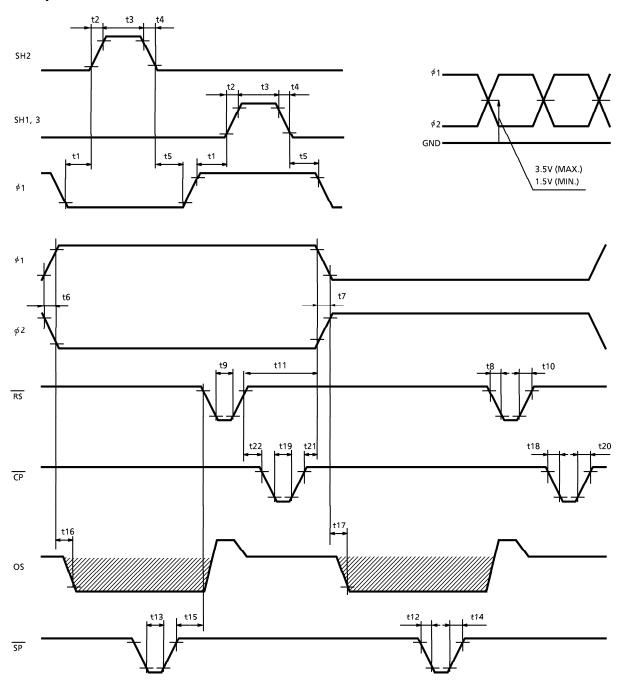
- (Note 11) $V_{\phi}0$, E"H" means the high level voltage of $V_{\phi}0$ and $V_{\phi}E$ when SH pulse is high
- (Note 12) Supply "L" level to \overline{SP} terminal when sample-and-hold circuit is not used. (Note 13) Supply \overline{SH} (inversed pulse of SH) to \overline{CP} terminal when clamp circuit is not used.

CLOCK CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Clock Pulse Frequency	f∳	_	0.5	2.0	MHz
Reset Pulse Frequency	fRS	_	1.0	4.0	MHz
Sample and Hold Pulse Frequency	f <u>₹</u> P	_	1.0	4.0	MHz
Clamp Pulse Frequency	f <u>CP</u>	_	1.0	4.0	MHz
Clock Capacitance	C ø 0, E	_	500	_	pF
Final Stage Clock Capacitance	C∮B	_	10	_	pF
Shift Gate Capacitance	C _{SH}	_	200	_	pF
Reset Gate Capacitance	CRS	_	10	_	pF
Sample and Hold Gate Capacitance	CSP	_	10	_	pF
Clamp Gate Capacitance	ССР	_	10	_	pF



TIMING REQUIREMENTS

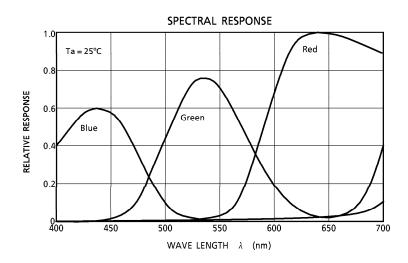


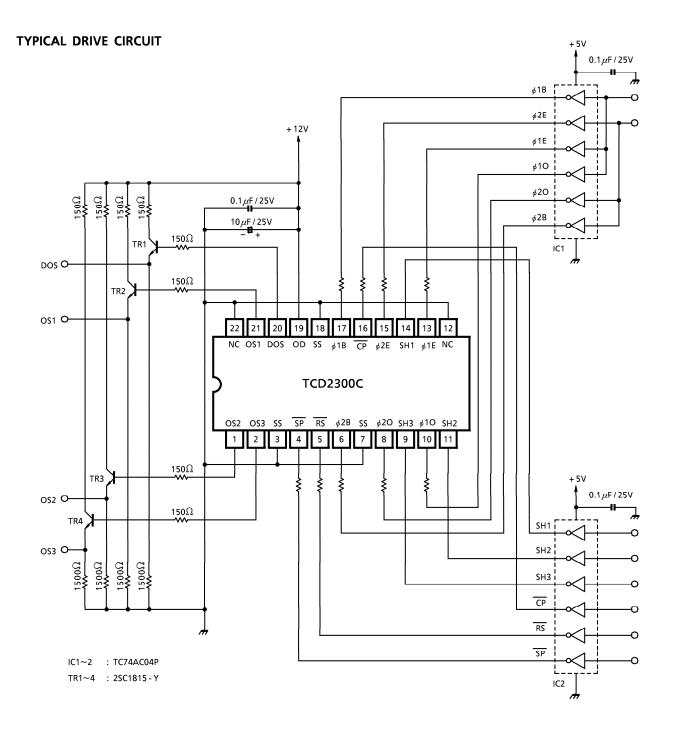
TIMING REQUIREMENTS (Cont'd)

CHARACTERISTIC	SYMBOL	MIN.	TYP. (Note 14)	MAX.	UNIT
Pulse Timing of SH and ϕ 0, E	t1, t5	0	1000	_	ns
SH Pulse Rise Time, Fall Time	t2, t4	0	50	_	ns
SH Pulse Width	t3	500	1000	_	ns
ϕ 1, ϕ 2 Pulse Rise Time, Fall Time	t6, t7	0	50	_	ns
RS Pulse Rise Time, Fall Time	t8, t10	0	20	_	ns
RS Pulse Width	t9	40	250	_	ns
Pulse Timing of ϕ 1B, ϕ 2B and \overline{RS}	t11	120	300	_	ns
SP Pulse Rise Time, Fall Time	t12, t14	0	20	_	ns
SP Pulse Width	t13	70	100	_	ns
Pulse Timing of SP and RS	t15	0	50	_	ns
Video Data Delay Time (Note 15)	t16, t17	<u> </u>	70	_	ns
CP Pulse Rise Time, Fall Time	t18, t20	0	20	_	ns
CP Pulse Width	t19	100	200	_	ns
Pulse Timing of ϕ 1B, ϕ 2B and $\overline{\sf CP}$	t21	20	50	_	ns
Pulse Timing of RS and CP	t22	0	50		ns

(Note 14) TYP. is the case of $f\overline{RS}$ = 1.0MHz (Note 15) Load Resistance is $100k\Omega$

TYPICAL SPECTRAL RESPONSE





CAUTION

1. Window Glass

The dust and stain on the glass window of the package degrade optical performance of CCD sensor.

Keep the glass window clean by saturating a cotton swab in alcohol and lightly wiping the surface, and allow the glass to dry, by blowing with filtered dry N2.

Care should be taken to avoid mechanical or thermal shock because the glass window is easily to damage.

2. Electrostatic Breakdown

Store in shorting clip or in conductive foam to avoid electrostatic breakdown.

3. Incident Light

CCD sensor is sensitive to infrared light.

Note that infrared light component degrades resolution and PRNU of CCD sensor.

4. Lead Frame Forming

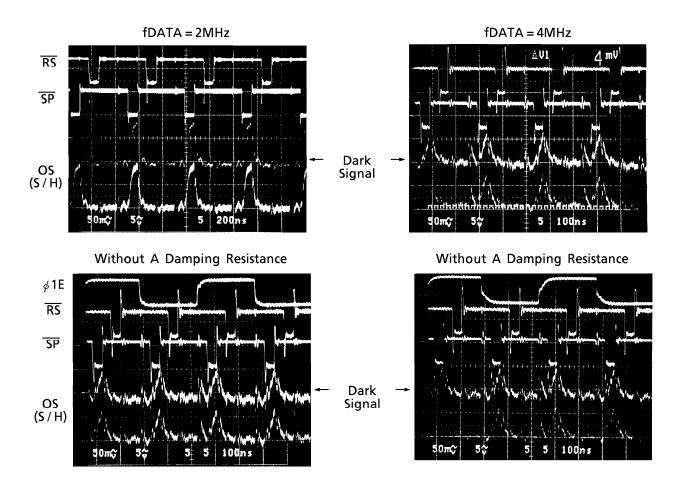
Since this package is not shoutagainst mechanical stress, you should not reform the lead frame. We recommend to use a IC-inserter when you assemble to PCB.

<Application note>

EVEN-ODD UNBALANCE

When High-speed draiving standard level of odd-even bits is often unbalanced. For that reason when high-speed draiving CCD you should put a damping resistance in input ϕ pin.

1. WAVEFORM (Sample and Hold ON)

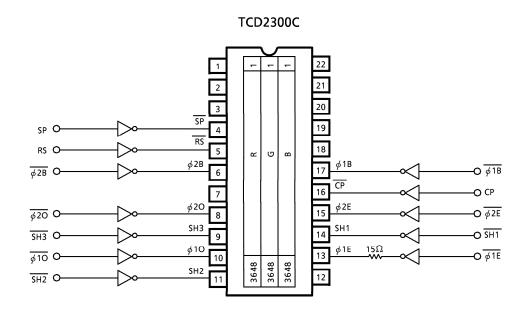


2. MEASUREMENT CONDITION

Ta = 25°C, $V_{AD} = V_{DD} = 12V$, $V_{\phi 1E} = V_{\phi 1B} = V_{\phi 1B} = V_{\phi 2E} = V_{\phi 2B} = V_{\overline{RS}} = V_{\overline{CP}} = V_{\overline{SP}} = V_{SH1} = V_{SH2} = V_{SH3} = 5V$ (Pulse), Light Source = Daylight Fluorescent Lamp.

Ocilloscope	Tektoronix	2465A (400MHz)
Probe	P6136	10.8pF

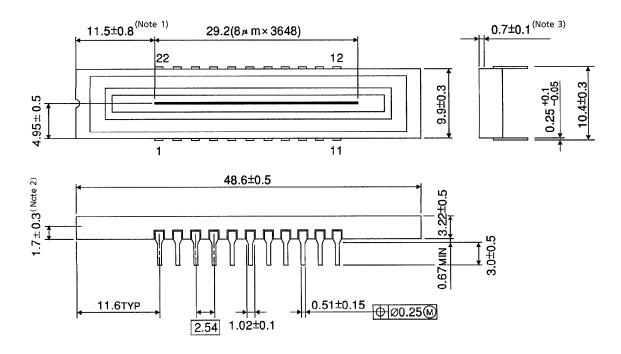
3. DRIVE CIRCUIT (with a damping resistance) Please put a damping resistance in input ϕ 1E (15 Ω).



OUTLINE DRAWING

WDIP22-C-400-2.54A (C)

Unit: mm



(Note 1) No. 1 SENSOR ELEMENT (S1) TO EDGE OF PACKAGE.

(Note 2) TOP OF CHIP TO BOTTOM OF PACKAGE.

(Note 3) GLASS THICKNES (n = 1.5)

Weight: 4.8g (Typ.)